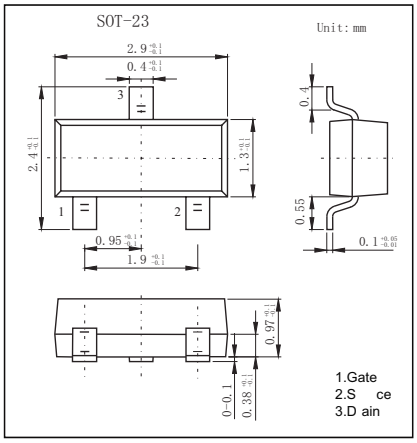
ŏ TrenchFET Power MOSFET

ŏ N-Channel Enhancement Mode Field Effect Transistor

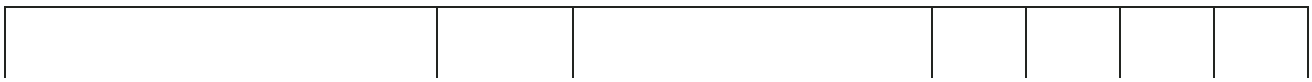
ŏCase style:SOT-23molded plastic

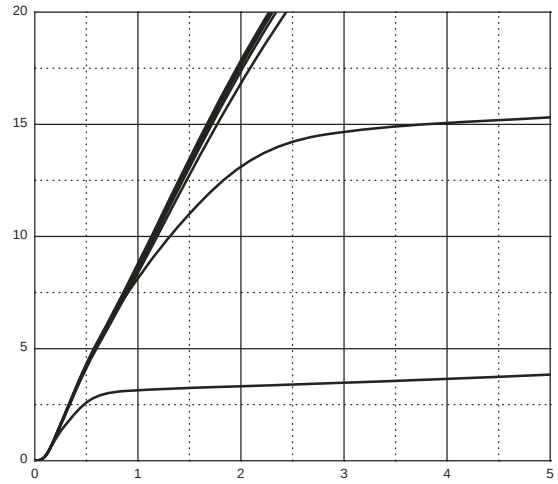
ŏMounting position:any

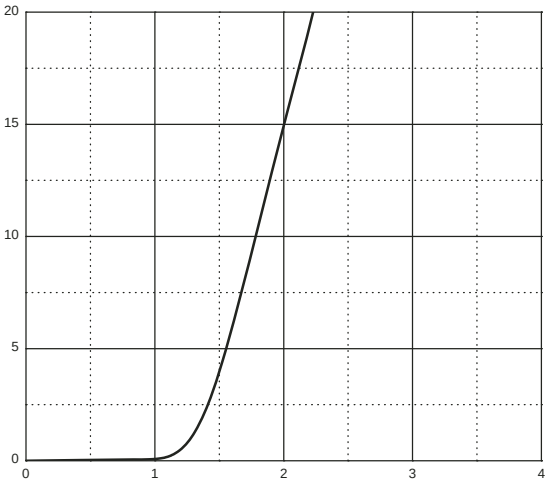


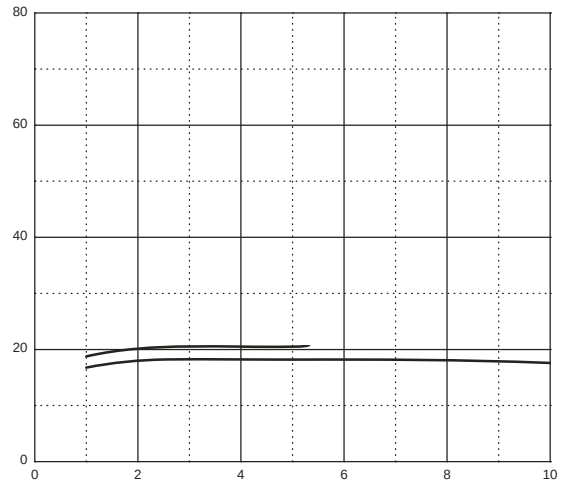
@ 25ÁC Ambient Temperature (unless otherwise noted)

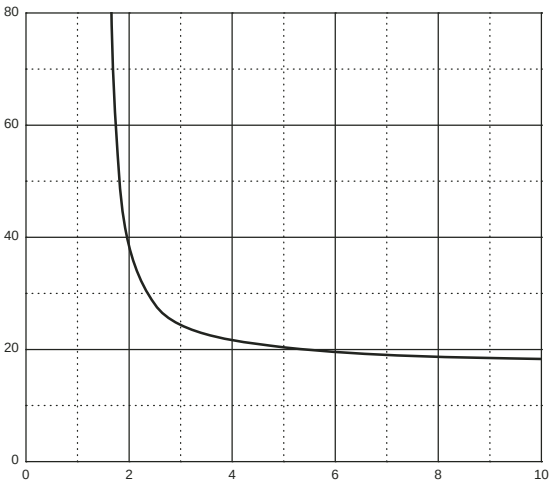
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	ῶ/W
Junction Temperature	T_J	150	ῶ
Storage Temperature	T_{stg}	-55 ~+150	

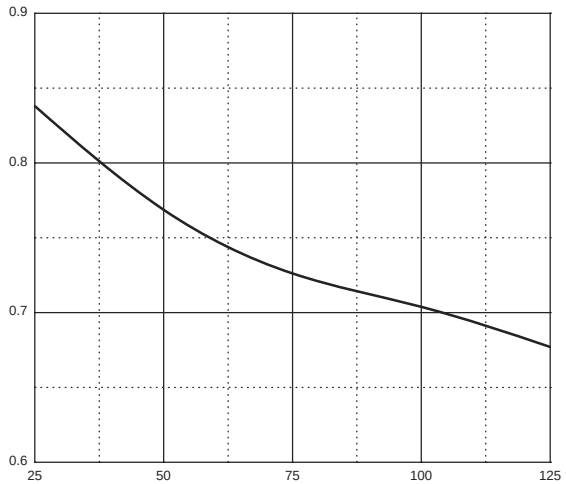


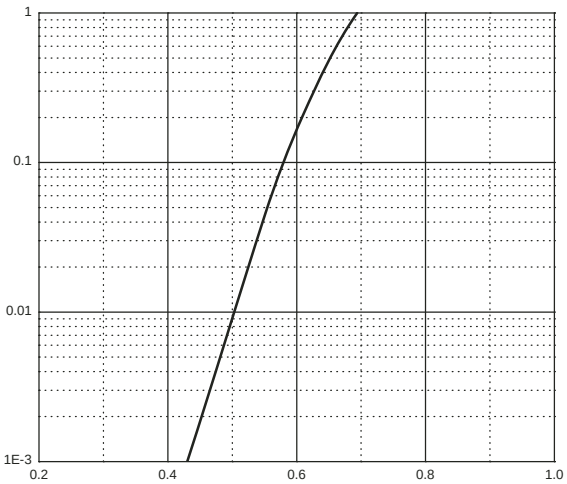

20
15
10
5
0
0
1
2
3
4
5


20
15
10
5
0
0
1
2
3
4


80
60
40
20
0
0
2
4
6
8
10


80
60
40
20
0
0
2
4
6
8
10


0.9
0.8
0.7
0.6
25
50
75
100
125


1
0.1
0.01
1E-3
0.2
0.4
0.6
0.8
1.0